

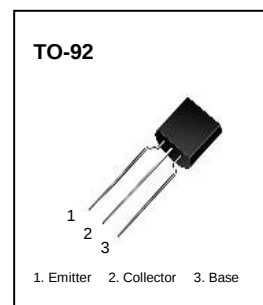


PTM928

PNP Epitaxial Silicon Transistor
-2 Amperes / 1 Watts

Audio Power Amplifier

- Complement to PTM2328
- 3 Watt Output Application



Absolute Maximum Ratings

TC=25℃ unless otherwise noted

CHARACTERISTICS	SYMBOL	RATING	UNIT
Collector-Base Voltage	V_{CBO}	-60	V
Collector-Emitter Voltage	V_{CEO}	-55	V
Emitter-Base Voltage	V_{EBO}	-7	V
Collector Current (DC)	I_C	-2	A
Collector Dissipation (Tc=25℃)	P_C	1	W
Junction Temperature	T_J	150	℃
Storage Temperature	T_{STG}	-65~150	℃

Electrical Characteristics

TC=25℃ unless otherwise noted

CHARACTERISTICS	SYMBOL	Test Condition	Min	Typ.	Max	Unit
Collector-Base Breakdown Voltage	BV_{CBO}	$I_C=-100\mu A, I_B=0$	-60			V
Collector-Emitter Breakdown Voltage	BV_{CEO}	$I_C=-1mA, I_B=0$	-55			V
Emitter-Base Breakdown Voltage	BV_{EBO}	$I_C=-100\mu A, I_B=0$	-7			V
Collector Cut-off Current	I_{CBO}	$V_{EB}=60V, I_C=0$			500	nA
Emitter Cut-off Current	I_{EBO}	$V_{EB}=5V, I_C=0$			500	nA
DC Current Gain	h_{FE}	$V_{CE}=-2V, I_C=-1A$	140		320	
*Collector-Emitter Saturation Voltage	$V_{CE(sat)}$	$I_C=-2A, I_B=-0.2A$		-0.4	-0.55	V
*Base-Emitter Saturation Voltage	$V_{BE(sat)}$	$I_C=-2A, I_B=-0.2A$		-1.0	-1.5	V
Output Capacitance	C_{ob}	$V_{CB}=-10V, f=0.1MHz$		48		pF
Current Gain Bandwidth Product	f_T	$V_{CE}=-2V, I_C=-0.5A$		120		MHz

* Pulse Test: Pulse Width≤250μs, Duty Cycle≤2%

Typical Characteristics

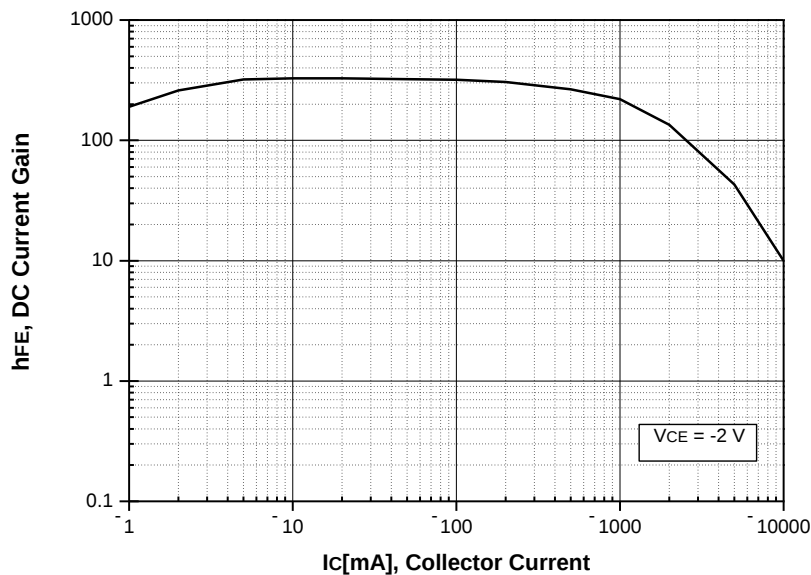


Figure 1. DC Current Gain

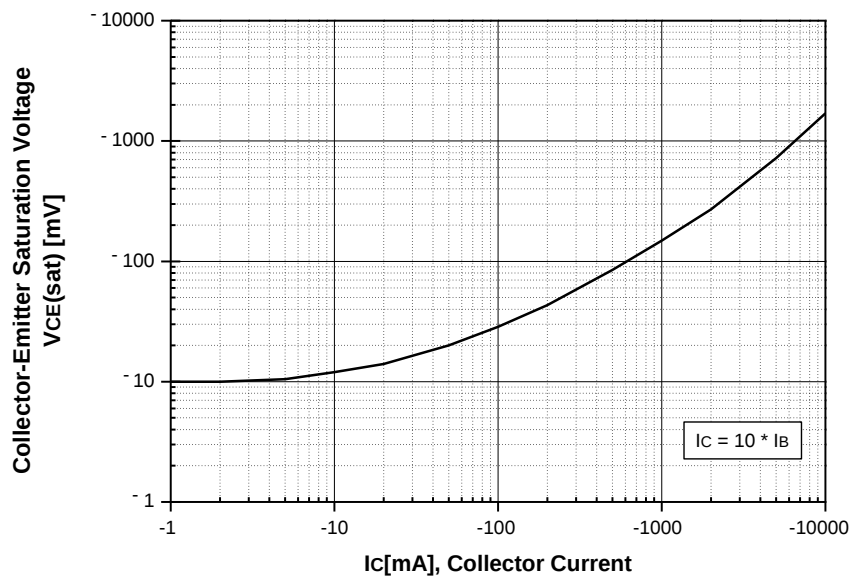


Figure 2. Collector-Emitter Saturation Voltage

Typical Characteristics

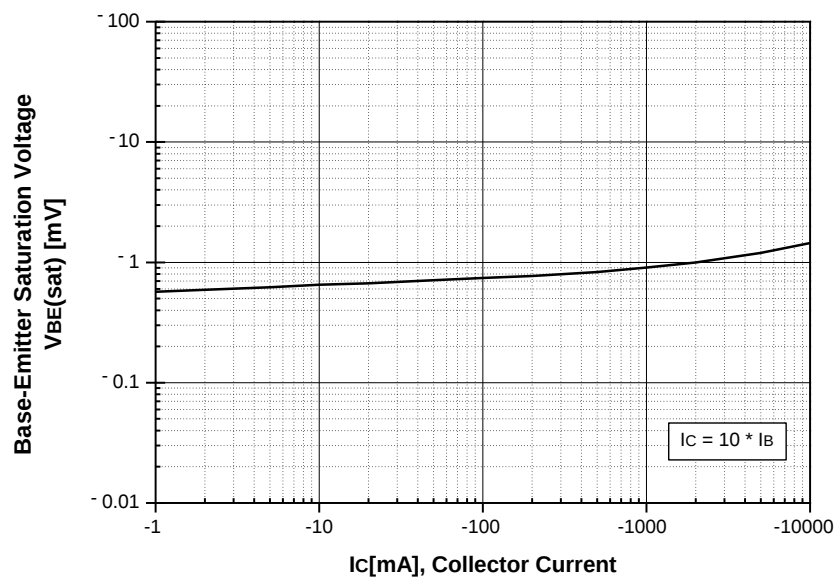


Figure 3. Base-Emitter Saturation Voltage

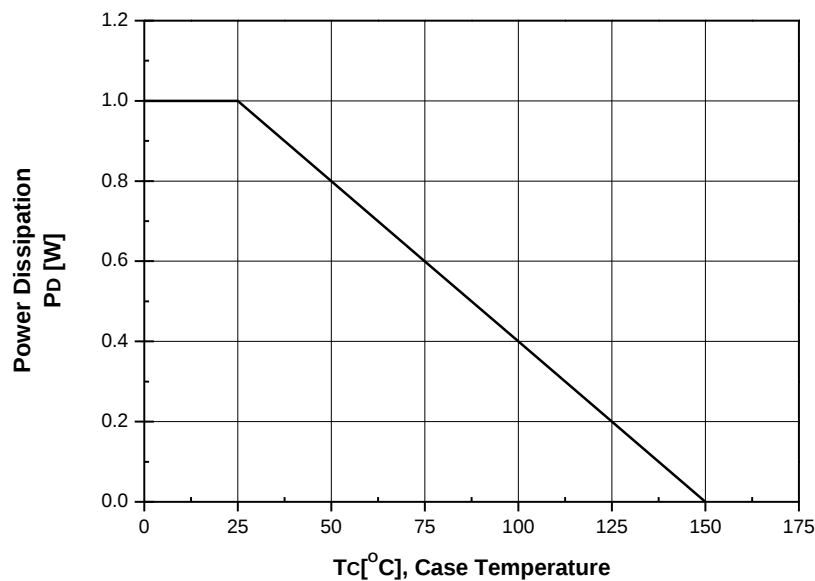


Figure 4. Power Derating